RAVINDRA COLLEGE OF ENGINEERING FOR WOMEN

II B tech -I Semester (R19)
Branch: ECE
Academic year 2020-21
Subject : Electronic Devices and Circuits(19A04302T)

UNIT: 5

S No	Questions (Short)	CO	Cognitive Level
1	Draw the symbol for N-channel E-MOSFET.	C202.5	Remember
2	Compare BJT and FET amplifiers.	C202.5	Remember
3	What is the need of biasing?	C202.6	Remember
4	Write the equation for drain current of JFET	C202.5	Remember
5	Write about two types of MOSFETs	C202.5	Remember
6	Write any two differences between N-channel JFET to a P-channel JFET.	C202.5	Remember

S No	Questions (Essay)	CO	Cognitive Level
1	How should the gate-source junction of a JFET be biased? Explain how the potential applied to this junction controls the drain current.	C202.6	Analyse
2	Sketch the cross section of an NMOS enhancement transistor and briefly explain.	C202.5	Apply
3	Draw two biasing circuits for an enhancement type MOSFET and explain.	C202.6	Apply
4	Why we call FET as a voltage controlled device?	C202.5	Analyse
5	Draw the drain characteristics of depletion type MOSFET. Explain clearly different operating regions in characteristics with proper reasoning.	C202.6	Apply
6	Explain the principle of MOSFET in depletion mode with neat sketches and o/p characteristics.	C202.5	Understand
7	Explain the different parameters of FET.	C202.5	Understand
8	Explain the voltage divider biasing circuit of FET.	C202.5	Understand
9	Draw and explain the drain characteristics of N-channel Enhancement type MOSFET.	C202.5	Apply
10	Draw and explain construction and operation of Enhancement mode MOSFET with its characteristics.	C202.5	Apply